



**TECH PUBLIC**  
台舟电子

**SI4435DY**

P-Channel Enhancement Mode Power MOSFET

[www.sot23.com.tw](http://www.sot23.com.tw)

## GENERAL FEATURES

- $V_{DS} = -30V, I_D = -12A$
- $R_{DS(ON)}(\text{Typ.}) 9.5m\Omega @ V_{GS}=-10V$
- $R_{DS(ON)}(\text{Typ.}) 14m\Omega @ V_{GS}=-4.5V$

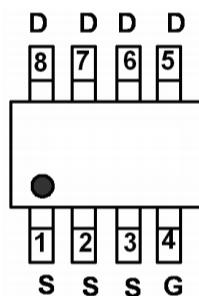
## Application

- PWM applications
- Load switch
- Power management

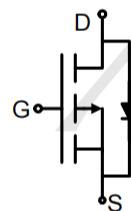
## Package and Pin Configuration



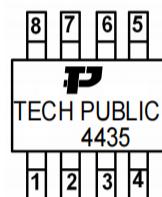
SOP-8 top view



## Circuit diagram



## Marking:



## Absolute Maximum Ratings ( $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	-12	A
Drain Current-Pulsed <sup>(Note 1)</sup>	$I_{DM}$	-48	A
Maximum Power Dissipation	$P_D$	3	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	°C

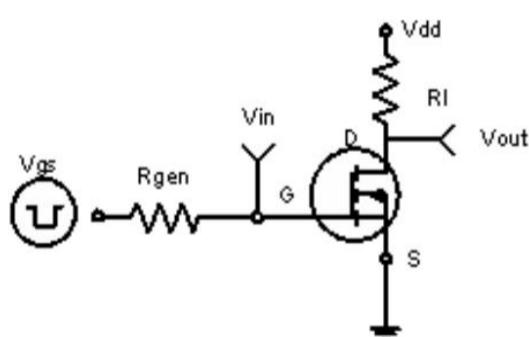
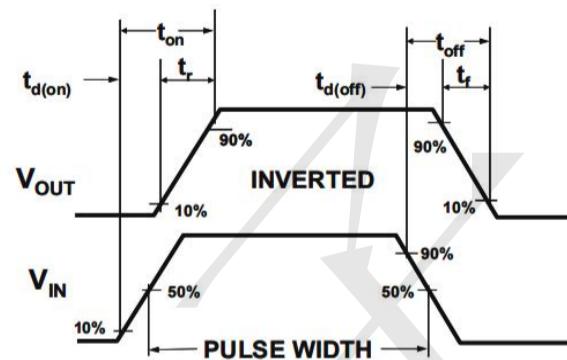
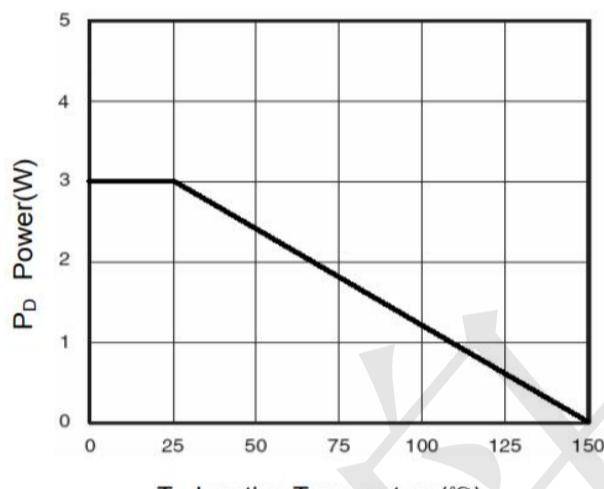
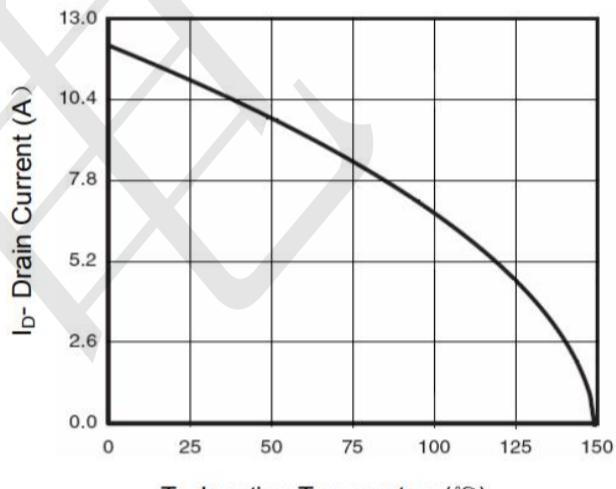
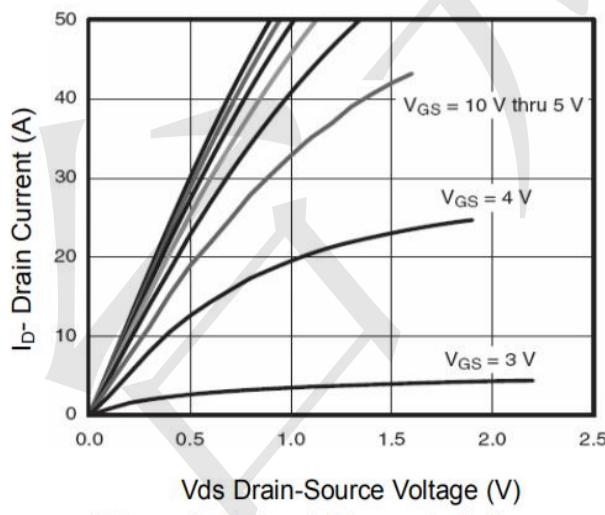
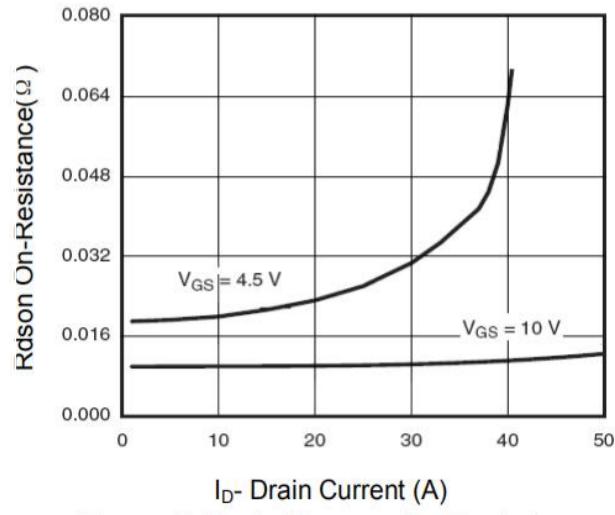
## Thermal CharacteristicE

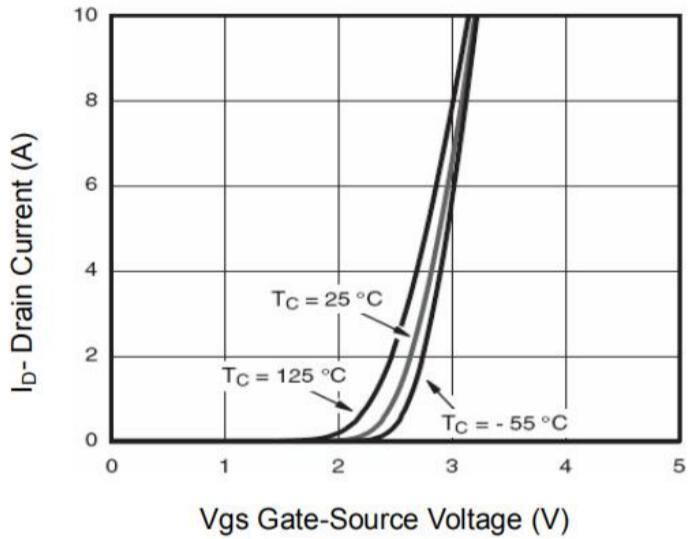
Thermal Resistance, Junction-to-Ambient <sup>(Note 2)</sup>	$R_{\theta JA}$	41.67	°C/W
---	-----------------	-------	------



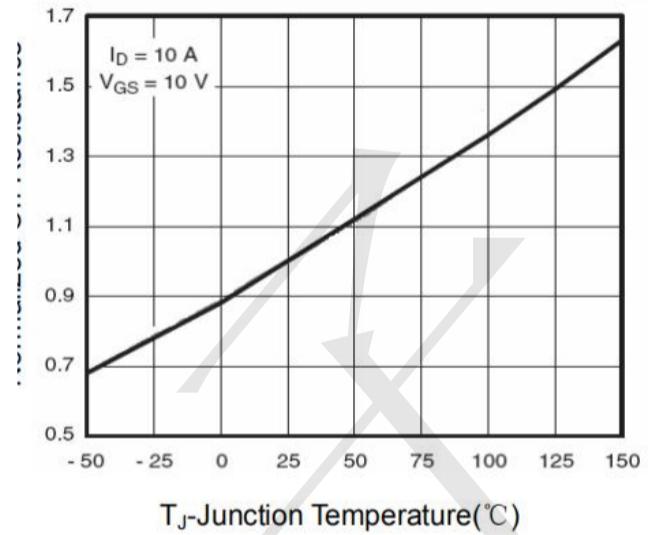
**Electrical Characteristics ( $T_A=25^\circ\text{C}$  unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$\text{BV}_{\text{DSS}}$	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=-250\mu\text{A}$	-30		-	V
Zero Gate Voltage Drain Current	$I_{\text{DSS}}$	$V_{\text{DS}}=-30\text{V}, V_{\text{GS}}=0\text{V}$	-	-	-1	$\mu\text{A}$
Gate-Body Leakage Current	$I_{\text{GSS}}$	$V_{\text{GS}}=\pm20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	$\pm100$	nA
<b>On Characteristics</b> (Note 3)						
Gate Threshold Voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=-250\mu\text{A}$	-1	-1.5	-3	V
Drain-Source On-State Resistance	$R_{\text{DS(ON)}}$	$V_{\text{GS}}=-10\text{V}, I_{\text{D}}=-10\text{A}$	-	9.5	13	$\text{m}\Omega$
		$V_{\text{GS}}=-4.5\text{V}, I_{\text{D}}=-7\text{A}$	-	14	19	$\text{m}\Omega$
Forward Transconductance	$g_{\text{FS}}$	$V_{\text{DS}}=-10\text{V}, I_{\text{D}}=-10\text{A}$	20	-	-	S
<b>Dynamic Characteristics</b> (Note 4)						
Input Capacitance	$C_{\text{iss}}$	$V_{\text{DS}}=-15\text{V}, V_{\text{GS}}=0\text{V}, F=1.0\text{MHz}$	-	1200	-	PF
Output Capacitance	$C_{\text{oss}}$		-	200	-	PF
Reverse Transfer Capacitance	$C_{\text{rss}}$		-	150	-	PF
<b>Switching Characteristics</b> (Note 4)						
Turn-on Delay Time	$t_{\text{d(on)}}$	$V_{\text{DD}}=-15\text{V}, I_{\text{D}}=-10\text{A}, V_{\text{GS}}=-10\text{V}, R_{\text{GEN}}=1\Omega$	-	11	-	nS
Turn-on Rise Time	$t_r$		-	6	-	nS
Turn-Off Delay Time	$t_{\text{d(off)}}$		-	28	-	nS
Turn-Off Fall Time	$t_f$		-	10	-	nS
Total Gate Charge	$Q_g$	$V_{\text{DS}}=-15\text{V}, I_{\text{D}}=-10\text{A}, V_{\text{GS}}=-10\text{V}$	-	25	-	nC
Gate-Source Charge	$Q_{\text{gs}}$		-	3.9	-	nC
Gate-Drain Charge	$Q_{\text{gd}}$		-	4.8	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	$V_{\text{SD}}$	$V_{\text{GS}}=0\text{V}, I_{\text{s}}=-2\text{A}$	-	-	-1.2	V

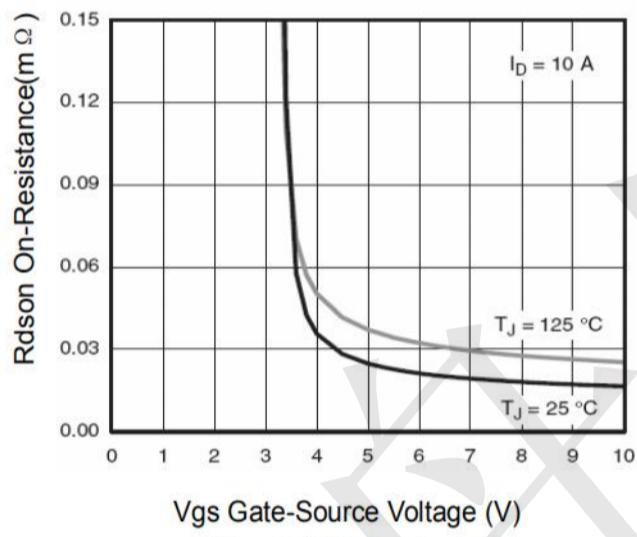
**Typical Electrical and Thermal Characteristics**

**Figure 1:Switching Test Circuit**

**Figure 2:Switching Waveforms**

**Figure 3 Power Dissipation**

**Figure 4 Drain Current**

**Figure 5 Output Characteristics**

**Figure 6 Drain-Source On-Resistance**



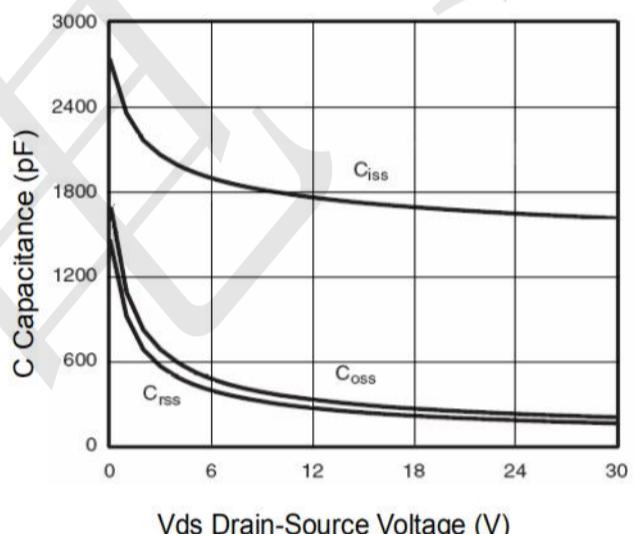
**Figure 7 Transfer Characteristics**



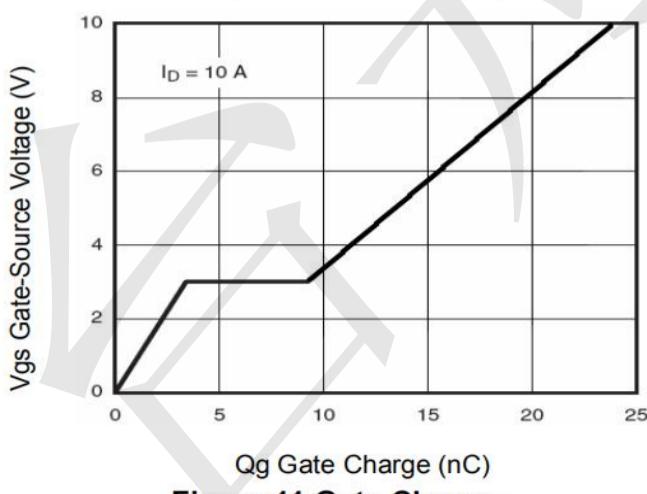
**Figure 8 Drain-Source On-Resistance**



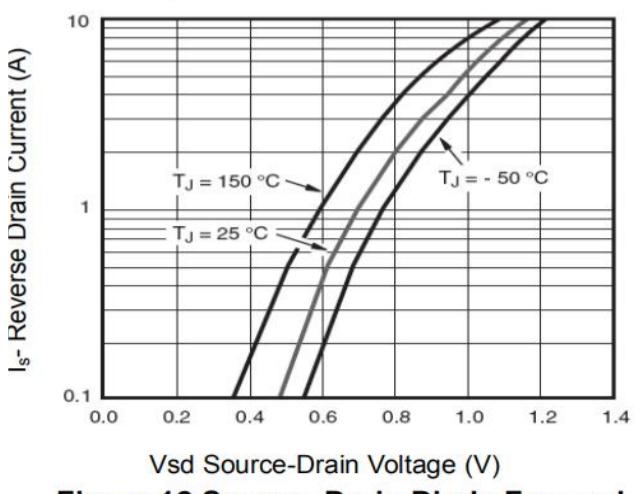
**Figure 9 R<sub>DSON</sub> vs V<sub>G</sub>**



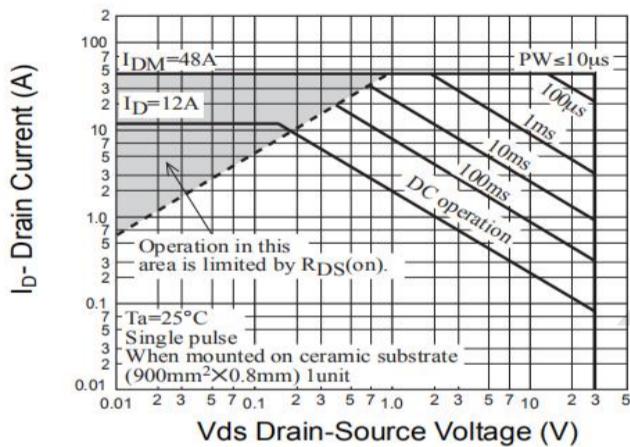
**Figure 10 Capacitance vs V<sub>D</sub>**



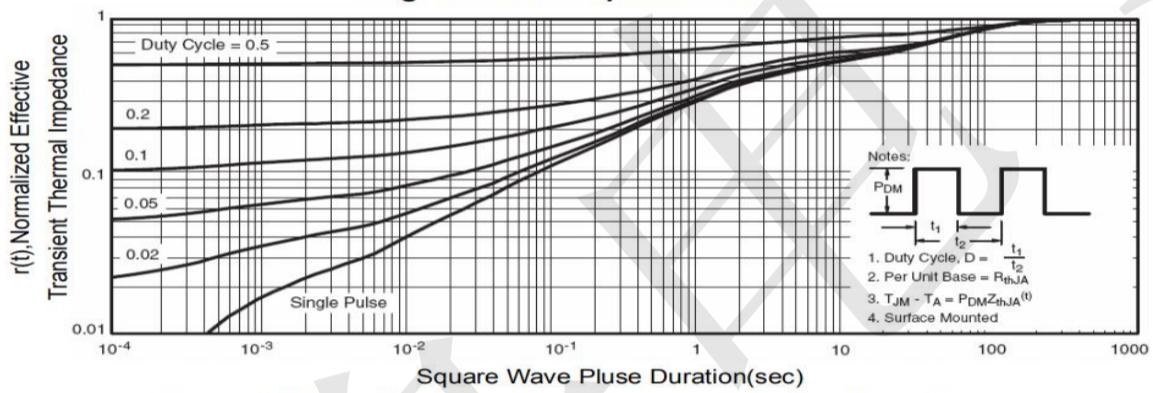
**Figure 11 Gate Charge**



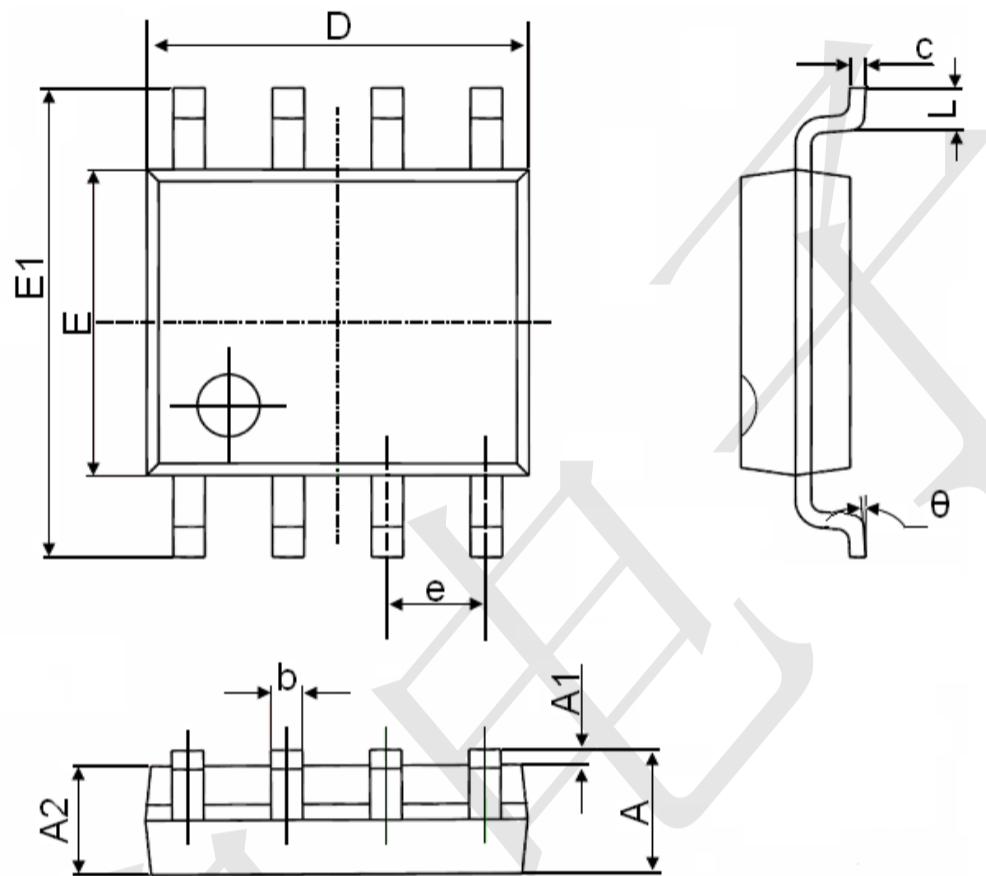
**Figure 12 Source-Drain Diode Forward**



**Figure 13 Safe Operation Area**



**Figure 14 Normalized Maximum Transient Thermal Impedance**

**SOP-8 Package Information**

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

# X-ON Electronics

Largest Supplier of Electrical and Electronic Components

***Click to view similar products for RF MOSFET Transistors category:***

***Click to view products by TECH PUBLIC manufacturer:***

Other Similar products are found below :

[FH2164](#) [BLF245](#) [ARF465BG](#) [BF 2030 E6814](#) [BLF861A](#) [MRF6S20010GNR1](#) [DU28200M](#) [MMRF1015NR1](#) [UF28100M](#) [MW6S010GNR1](#)  
[DU2820S](#) [MRF24301HR5](#) [MMRF1014NT1](#) [MRF422](#) [ARF468BG](#) [MAPHST0045](#) [A2T27S020NR1](#) [DU2860U](#) [MHT1803A](#) [VRF152GMP](#)  
[MRFE6VP5300NR1](#) [BF2040E6814HTSA1](#) [MRFE6VP5150NR1](#) [MMRF5014HR5](#) [LET9060S](#) [MRF136Y](#) [MRF175GV](#) [AFT27S010NT1](#)  
[AFT27S006NT1](#) [MRF1K50NR5](#) [BG 3130 H6327](#) [MRFE6VP5300NR1](#) [MRFE6VP5600HR6](#) [MRFX1K80HR5](#) [BF998E6327HTSA1](#)  
[AFM907NT1](#) [AFT05MS006NT1](#) [AFV10700HR5](#) [MRF141](#) [MRF492](#) [MRF141](#) [MRF171](#) [MRF172](#) [MRF174](#) [AFM906NT1](#) [BLF578XR,112](#)  
[TPM9305PD6](#) [CJU02N65](#) [FDS9926A](#) [AFT05MS031NR1](#)